

## Excellent Integrated System Limited

Stocking Distributor

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[IXYS Corporation](#)  
[DSB80C45HB](#)

For any questions, you can email us directly:  
[sales@integrated-circuit.com](mailto:sales@integrated-circuit.com)



**DSB80C45HB**

**Schottky Diode Gen <sup>2</sup>**

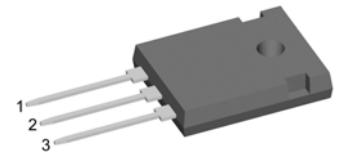
preliminary

$V_{RRM}$	=	45V
$I_{FAV}$	= 2x	40A
$V_F$	=	0.59V

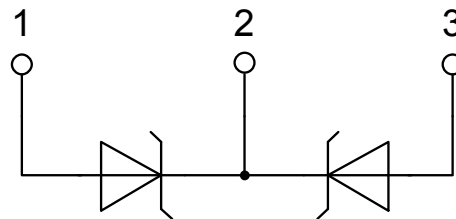
High Performance Schottky Diode  
 Low Loss and Soft Recovery  
 Common Cathode

Part number

**DSB80C45HB**



Backside: cathode



**Features / Advantages:**

- Very low  $V_f$
- Extremely low switching losses
- Low  $I_{rm}$  values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

**Applications:**

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

**Package:** TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

preliminary

Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage		$T_{VJ} = 25^{\circ}C$			45	V
$V_{RRM}$	max. repetitive reverse blocking voltage		$T_{VJ} = 25^{\circ}C$			45	V
$I_R$	reverse current, drain current	$V_R = 45 V$	$T_{VJ} = 25^{\circ}C$			15	mA
		$V_R = 45 V$	$T_{VJ} = 100^{\circ}C$			150	mA
$V_F$	forward voltage drop	$I_F = 40 A$	$T_{VJ} = 25^{\circ}C$			0.62	V
		$I_F = 80 A$				0.90	V
		$I_F = 40 A$	$T_{VJ} = 125^{\circ}C$			0.59	V
		$I_F = 80 A$				0.88	V
$I_{FAV}$	average forward current	$T_C = 125^{\circ}C$ rectangular $d = 0.5$	$T_{VJ} = 150^{\circ}C$			40	A
$V_{F0}$	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$			0.31	V
$r_F$	slope resistance					7	mΩ
$R_{thJC}$	thermal resistance junction to case					0.7	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.25		K/W
$P_{tot}$	total power dissipation		$T_C = 25^{\circ}C$			180	W
$I_{FSM}$	max. forward surge current	$t = 10 ms; (50 Hz), sine; V_R = 0 V$	$T_{VJ} = 45^{\circ}C$			600	A
$C_J$	junction capacitance	$V_R = 5 V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		1.38		nF
$E_{AS}$	non-repetitive avalanche energy	$I_{AS} = tbd A L = tbd \mu H$	$T_{VJ} = 25^{\circ}C$				mJ
$I_{AR}$	repetitive avalanche current	$V_A = 1.5 \cdot V_R$ typ.: $f = 10 kHz$					A

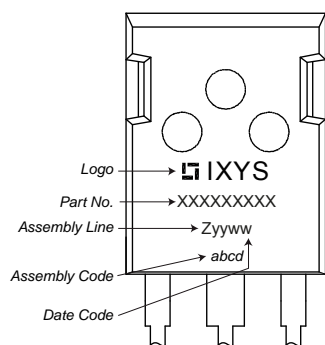


# DSB80C45HB

preliminary

Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal <sup>1)</sup>			50	A
$T_{VJ}$	virtual junction temperature		-55		150	°C
$T_{op}$	operation temperature		-55		125	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

### Product Marking



### Part number

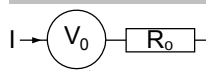
- D = Diode
- S = Schottky Diode
- B = ultra low VF
- 80 = Current Rating [A]
- C = Common Cathode
- 45 = Reverse Voltage [V]
- HB = TO-247AD (3)

Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSB80C45HB	DSB80C45HB	Tube	30	504883

### Equivalent Circuits for Simulation

\* on die level

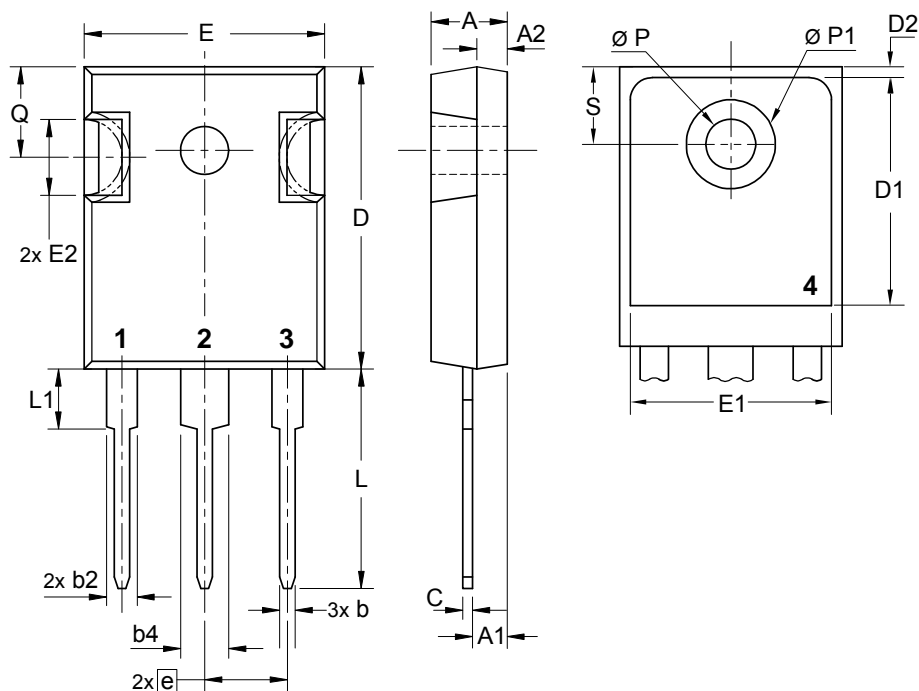
$T_{VJ} = 150\text{ °C}$



Schottky

$V_{0\ max}$	threshold voltage	0.31	V
$R_{0\ max}$	slope resistance *	4.5	mΩ

**Outlines TO-247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.215 BSC		5.46 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39

